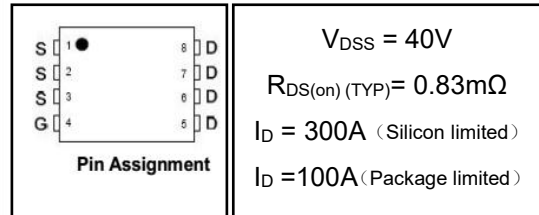


100A 40V N-channel Enhancement Mode Power MOSFET

1 Description

This N-channel enhancement mode power MOSFET utilizes advanced Split Gate Trench technology, which provides excellent $R_{DS(on)}$ and low Gate charge at the same time. Which accords with the RoHS standard.

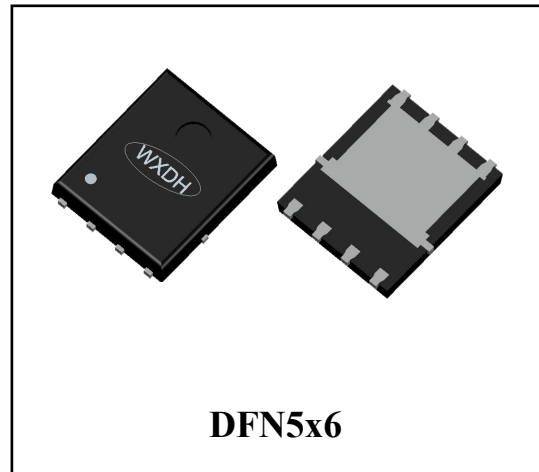


2 Features

- Low on resistance
- Low gate charge
- Fast switching
- Low reverse transfer capacitances
- 100% single pulse avalanche energy test
- 100% ΔV_{DS} test
- **AEC-Q101 qualified**

3 Applications

- Automotive application
- Battery management
- UPS (Uninterruptible Power Supplies)
- Synchronous Rectification for AC/DC Quick Charger



4 Electrical Characteristics

4.1 Absolute Maximum Ratings (Tc=25°C, unless otherwise noted)

Parameter		Symbol	Rating	Units
Drain-to-Source Voltage		V_{DSS}	40	V
Gate-to-Source Voltage		V_{GSS}	± 20	V
Continuous Drain Current	$T_C=25^\circ C$ (Silicon Limited)	I_D	300	A
	$T_C=25^\circ C$ (Package Limited)		100	A
	$T_C=100^\circ C$ (Package Limited)		100	A
Pulsed Drain Current ⁽¹⁾		I_{DM}	500	A
Single Pulse Avalanche Energy ⁽⁴⁾		E_{AS}	812	mJ
Avalanche Current ⁽⁴⁾		I_{AS}	57	A
Power Dissipation	$T_a=25^\circ C$	P_{tot}	2.5	W
	$T_C=25^\circ C$	P_{tot}	231	W
Junction Temperature Range		T_j	-55~175	$^\circ C$
Storage Temperature Range		T_{stg}	-55~175	$^\circ C$

4.2 Thermal Characteristics

Parameter	Symbol	Value		Units
		Typ	Max	
Thermal Resistance, Junction to Case-sink	R_{thJC}	0.65	0.85	$^\circ C/W$
Thermal Resistance, Junction to Ambient	R_{thJA}	60	78	$^\circ C/W$

4.3 Electrical Characteristics (Tc=25°C, unless otherwise noted)

Parameter	Symbol	Test Condition	Value			Units
			Min	Typ	Max	
Off Characteristics						
Drain-to-Source Breakdown Voltage	BV_{DSS}	$I_D=250\mu A, V_{GS}=0V$	40	45	--	V
Drain-to-Source Leakage Current	I_{DSS}	$V_{DS}=40V, V_{GS}=0V, T_C=25^\circ C$	--	--	-1	μA
		$V_{DS}=40V, V_{GS}=0V, T_C=125^\circ C$	--	--	-10	μA
Gate-to-Source Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$	--	--	± 100	nA
On Characteristics						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	1	--	2.5	V
Drain-to-Source on-state Resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=80A$	--	0.83	1.0	m Ω
		$V_{GS}=4.5V, I_D=80A$	--	1.2	1.5	
Dynamic Characteristics						
Input Capacitance	C_{iss}	$V_{GS}=0V, V_{DS}=20V, f=1.0MHz$	--	6087	--	pF
Output Capacitance	C_{oss}		--	2470	--	
Reverse Transfer Capacitance	C_{rss}		--	368	--	
Switching Characteristics						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=20V, I_D=80A, V_{GS}=10V, R_g=3\Omega$	--	38.6	--	nS
Turn-on Rise Time	t_r		--	15.3	--	
Turn-off Delay Time	$t_{d(off)}$		--	126	--	
Turn-off Fall Time	t_f		--	89	--	
Total Gate Charge	Q_g	$I_D=80A, V_{DD}=20V, V_{GS}=10V$	--	85	--	nC
Gate-to-Source Charge	Q_{gs}		--	23	--	
Gate-to-Drain("Miller") Charge	Q_{gd}		--	13	--	
Drain-Source Diode Characteristics						
Diode Forward Voltage ⁽³⁾	V_{SD}	$V_{GS}=0V, I_S=80A$	--	0.8	1.2	V
Diode Forward Current	I_S		--	--	100	A
Reverse Recovery Time	T_{rr}	$V_{DD}=20V, I_F=40A, di/dt=100A/\mu s, T_J=25^\circ C$	--	68.3	--	nS
Reverse Recovery Charge	Q_{rr}		--	87.8	--	nC

Notes:

- 1: Repetitive rating, pulse width limited by maximum junction temperature.
- 2: Surface mounted on FR4 Board, $t \leq 10$ sec.
- 3: Pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.
- 4: EAS condition : $L=0.5mH, V_{DD}=20V, V_G=10V, I_D=40A, Start T_J=25^\circ C$.

5 Typical characteristics diagrams

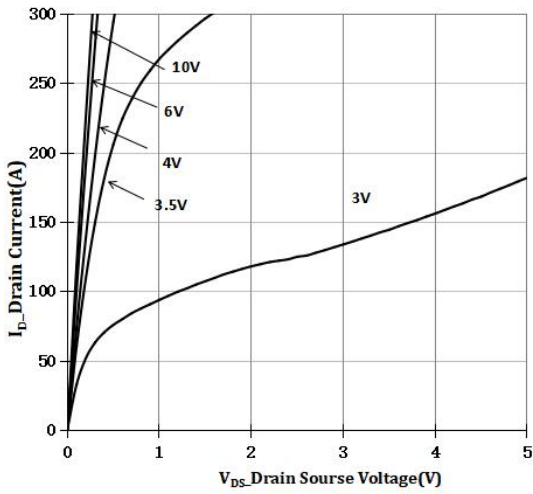


Fig 1 Output Characteristics

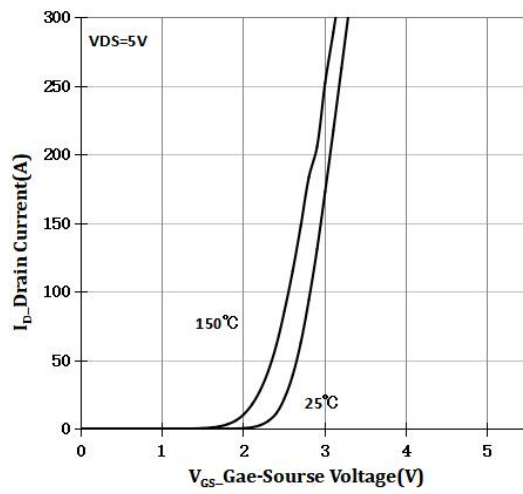


Fig 2 Transfer Characteristics

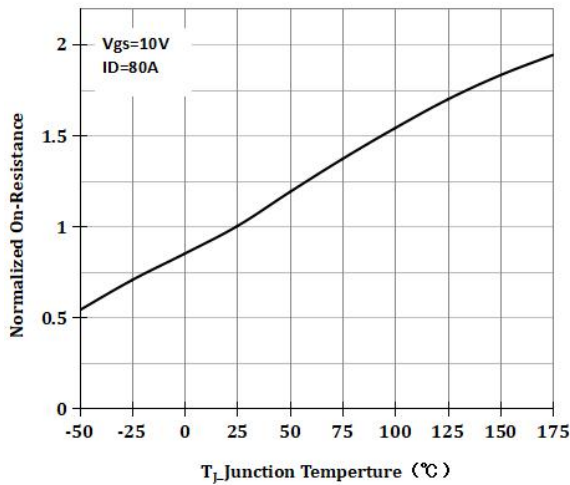


Fig 3 RDSON vs Junction Temperature

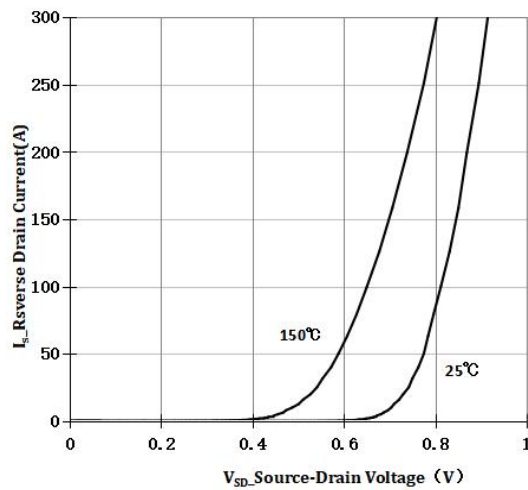


Fig 4 V_{SD}_ Source-Drain Diode forward

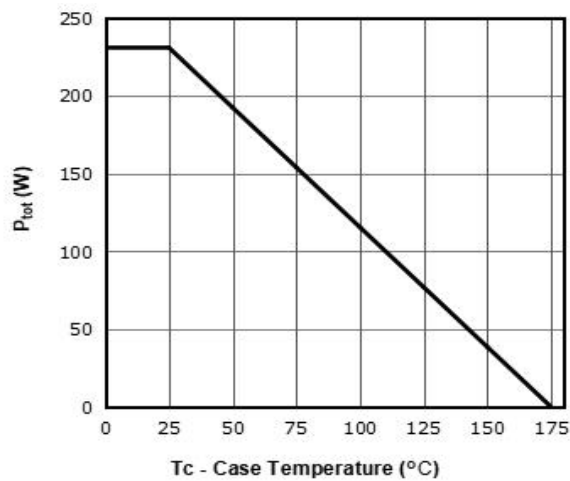


Fig 5 Power De-rating

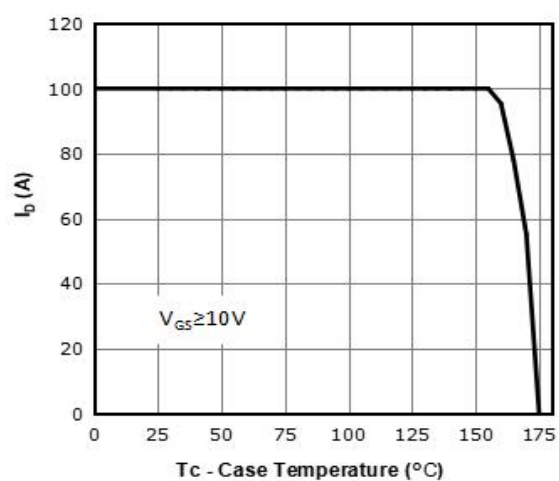


Fig 6 I_D Current De-rating

5 Typical characteristics diagrams

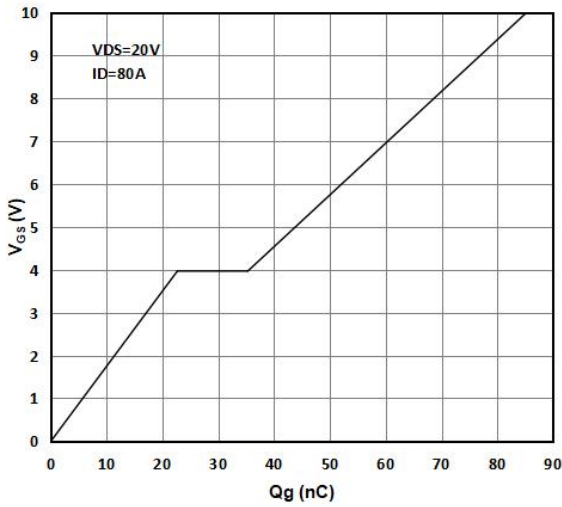


Fig 7 Gate Charge Figure

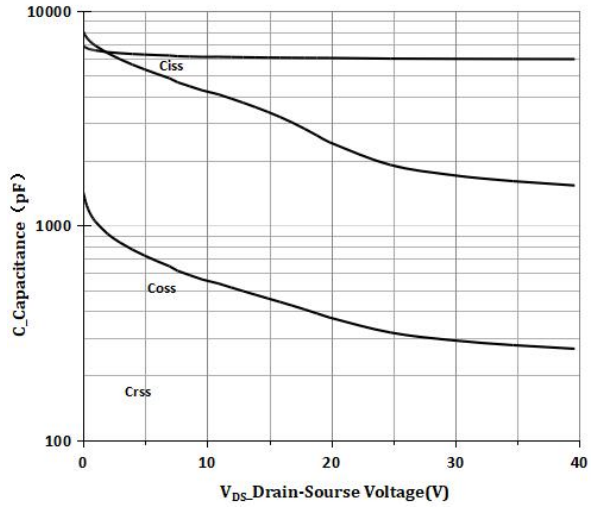


Fig 8 Capacitance vs Vds

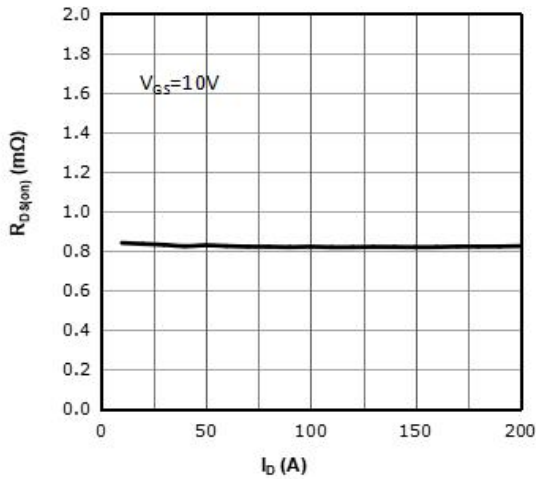


Fig 9 Rds(on) vs Drain Current

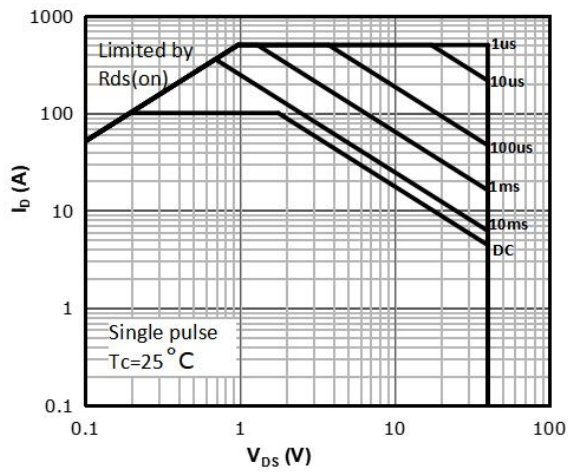


Fig 10 SOA

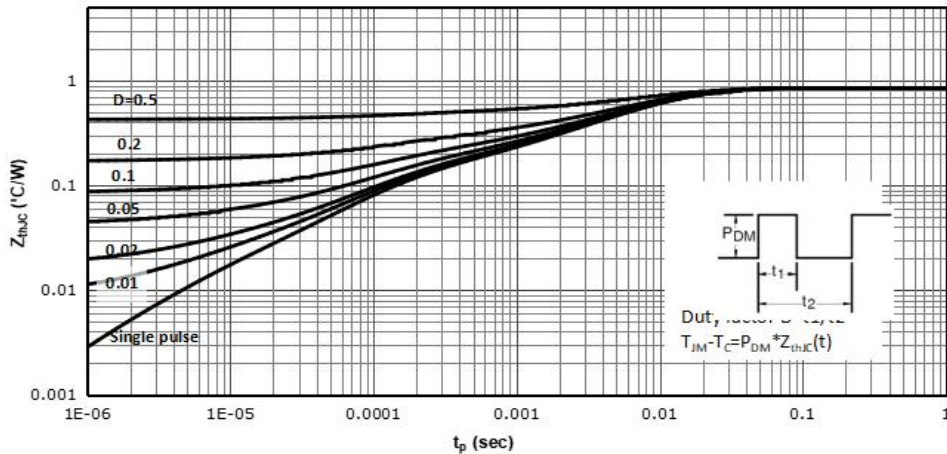
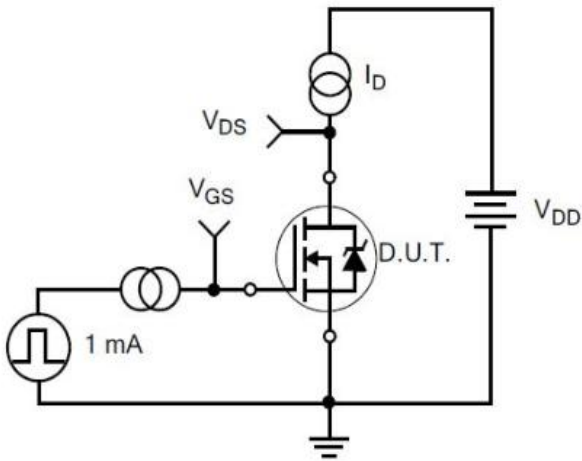
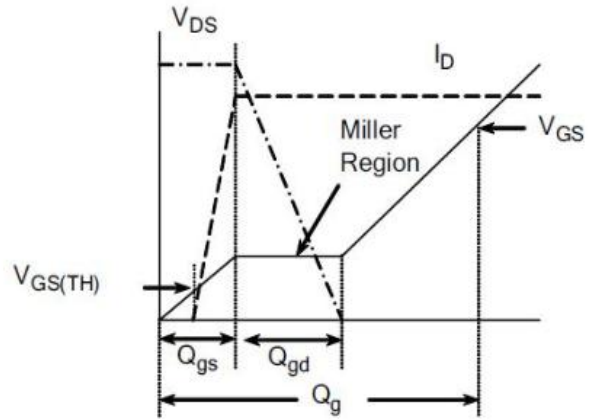


Fig 11 Normalized Maximum Transient Thermal Impedance

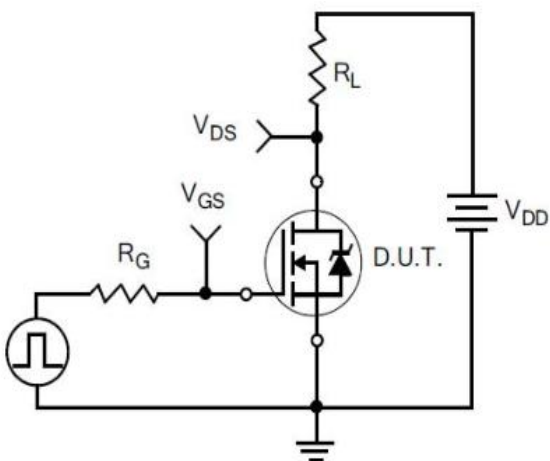
6 Typical Test Circuit and Waveform



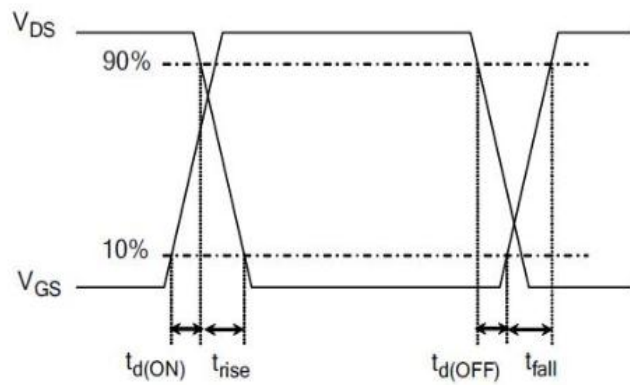
1) Gate Charge Test Circuit



2) Gate Charge Waveform

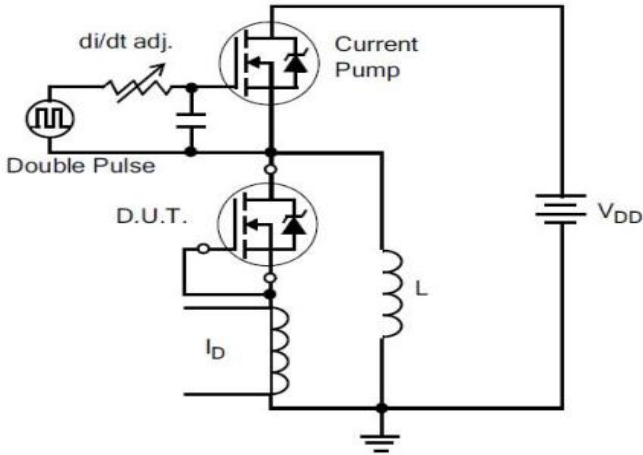


3) Resistive Switching Test Circuit

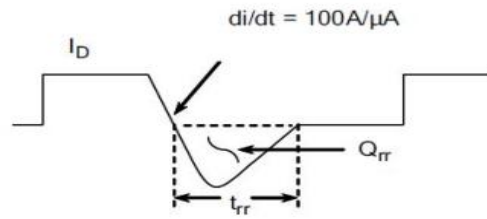


4) Resistive Switching Waveforms

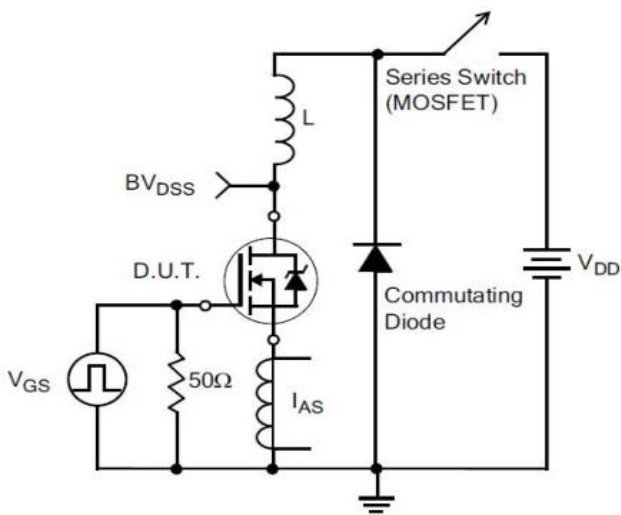
6 Typical Test Circuit and Waveform



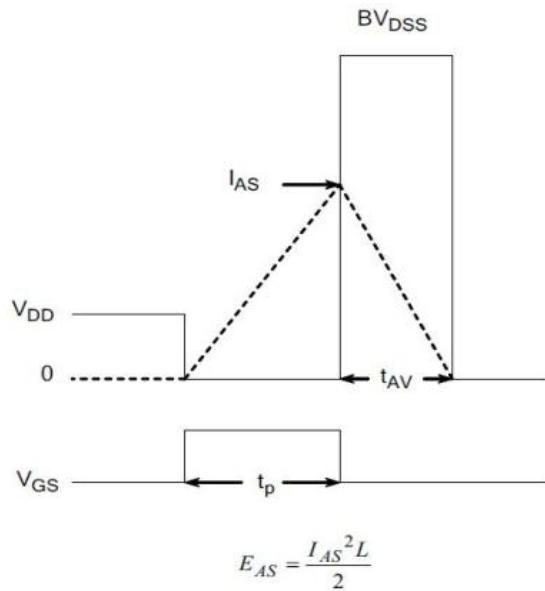
5) Diode Reverse Recovery Test Circuit



6) Diode Reverse Recovery Waveform

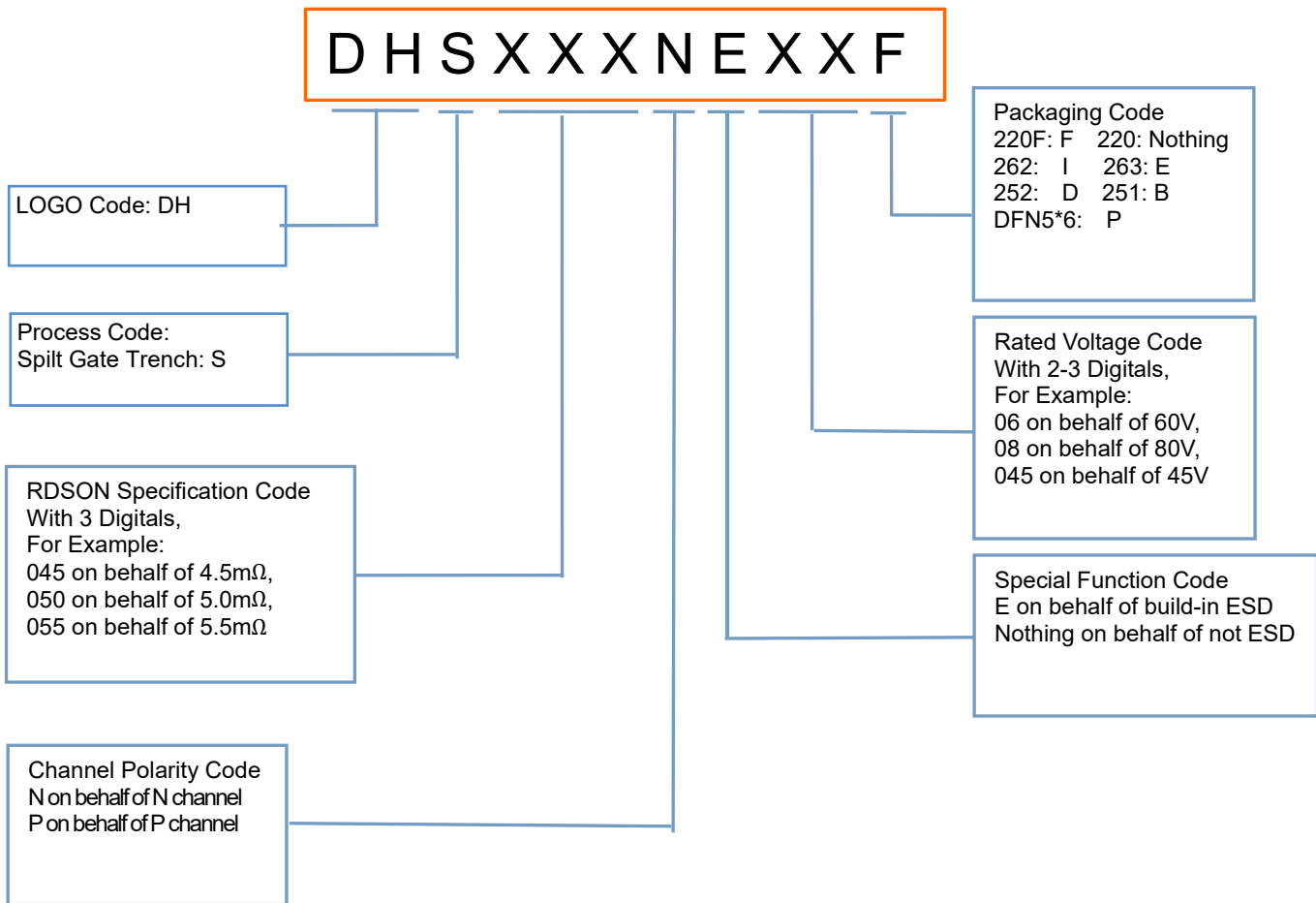


7) . Unclamped Inductive Switching Test Circuit



8) Unclamped Inductive Switching Waveforms

7 Product Names Rules



10 Attentions

- Jiangsu Donghai Semiconductor Technology CO.,LTD. reserves the right to change the specification without prior notice! The customer should obtain the latest version of the information before making the order and verify that the information is complete and up to date.
- It is the responsibility of the purchaser for any failure or failure of any semiconductor product under certain conditions. It is the responsibility of the purchaser to comply with safety standards and to take safety measures in the system design and machine manufacturing of Donghai products in order to avoid potential risk of failure. Injury or property damage.
- Product promotion is endless, our company will be dedicated to provide customers with better products.

11 Appendix

Revision history:

Date	REV.	Description	Page
2023.01.14	1.0	Original	10